80 V, 1 A NPN medium power transistors Rev. 9 — 25 October 2011

1. **Product profile**

1.1 General description

NPN medium power transistor series in Surface-Mounted Device (SMD) plastic packages.

Product overview Table 1.

Type number ^[1]	Package			PNP complement
	NXP	JEITA	JEDEC	
BCP56	SOT223	SC-73	-	BCP53
BCX56	SOT89	SC-62	TO-243	BCX53
BC56PA	SOT1061	-	-	BC53PA

[1] Valid for all available selection groups.

1.2 Features and benefits

- High current
- Three current gain selections
- High power dissipation capability
- Exposed heatsink for excellent thermal and electrical conductivity (SOT89, SOT1061)
- Leadless very small SMD plastic package with medium power capability (SOT1061)
- AEC-Q101 gualified

1.3 Applications

- Linear voltage regulators
- Low-side switches
- Battery-driven devices
- Power management
- MOSFET drivers
- Amplifiers

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	80	V
I _C	collector current		-	-	1	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	2	А
h _{FE}	DC current gain	$V_{CE} = 2 \text{ V}; I_{C} = 150 \text{ mA}$	<mark>[1]</mark> 63	-	250	
	h _{FE} selection -10	$V_{CE} = 2 \text{ V}; I_{C} = 150 \text{ mA}$	<u>[1]</u> 63	-	160	
	h _{FE} selection -16	$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 150 \text{ mA}$	<mark>[1]</mark> 100	-	250	

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta = 0.02$.



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2. Pinning information

Pin	Description	Simplified outline	Graphic symbo
SOT223			
1	base		
2	collector		2, 4
3	emitter		1
4	collector		3 sym016
SOT89			
1	emitter		
2	collector		2 J
3	base		31 sym042
SOT1061			
1	base	· · · · · · · · · · · · · · · · · · ·	
2	emitter	3	3
3	collector		
		1 2 Transparent top view	sym021

3. Ordering information

Table 4. Order	ring inform	ation						
Type number ^[1]	Package	Package						
	Name	Description	Version					
BCP56	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223					
BCX56	SC-62	plastic surface-mounted package; exposed die pad for good heat transfer; 3 leads	SOT89					
BC56PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body $2 \times 2 \times 0.65$ mm	SOT1061					

[1] Valid for all available selection groups.

BCP56_BCX56_BC56PA

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4. Marking

Table 5. Marking codes	
Type number	Marking code
BCP56	BCP56
BCP56-10	BCP56/10
BCP56-16	BCP56/16
BCX56	ВН
BCX56-10	ВК
BCX56-16	BL
BC56PA	AZ
BC56-10PA	ВК
BC56-16PA	BL

BCP56_BCX56_BC56PA

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5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	100	V
V _{CEO}	collector-emitter voltage	open base	-	80	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current		-	1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	2	А
I _B	base current		-	0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	0.3	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	BCP56		<u>[1]</u> _	0.65	W
			[2]	1.00	W
			[3]	1.35	W
	BCX56		<u>[1]</u> _	0.50	W
			[2]	0.95	W
			[3]	1.35	W
	BC56PA		<u>[1]</u> _	0.42	W
			[2]	0.83	W
			[3]	1.10	W
			[4] _	0.81	W
			<u>[5]</u>	1.65	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

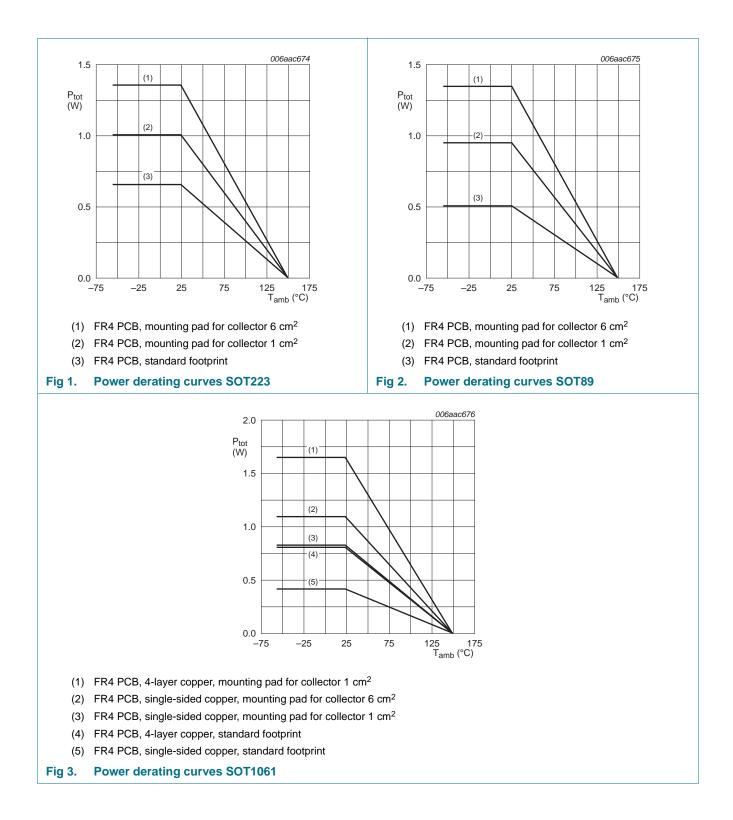
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

BCP56; BCX56; BC56PA



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6. Thermal characteristics

Table 7.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	BCP56		[1]	-	-	192	K/W
			[2]	-	-	125	K/W
			[3]	-	-	93	K/W
	BCX56		[1]	-	-	250	K/W
			[2]	-	-	132	K/W
			[3]	-	-	93	K/W
	BC56PA		[1]	-	-	298	K/W
			[2]	-	-	151	K/W
			[3]	-	-	114	K/W
			[4]	-	-	154	K/W
			[5]	-	-	76	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point						
	BCP56			-	-	16	K/W
	BCX56			-	-	16	K/W
	BC56PA			-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

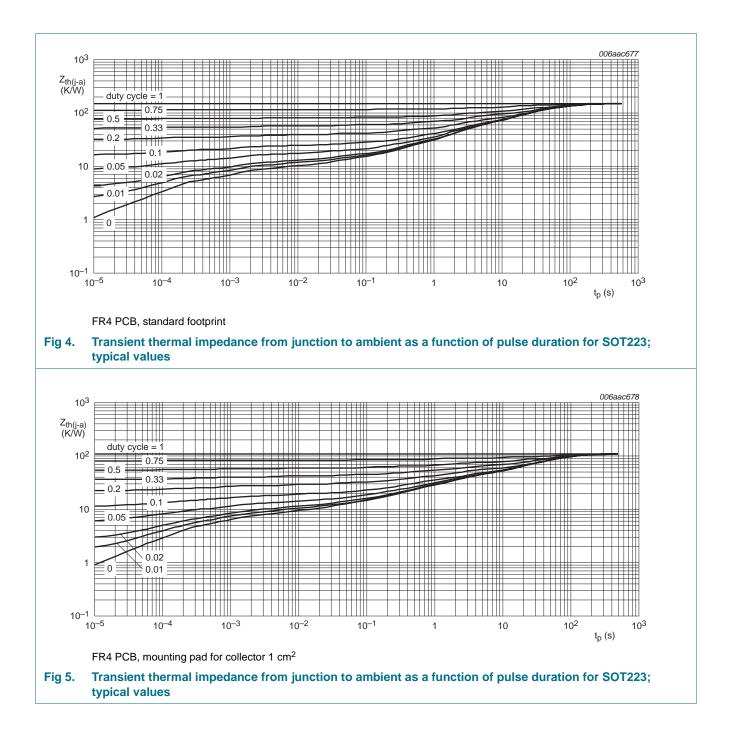
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

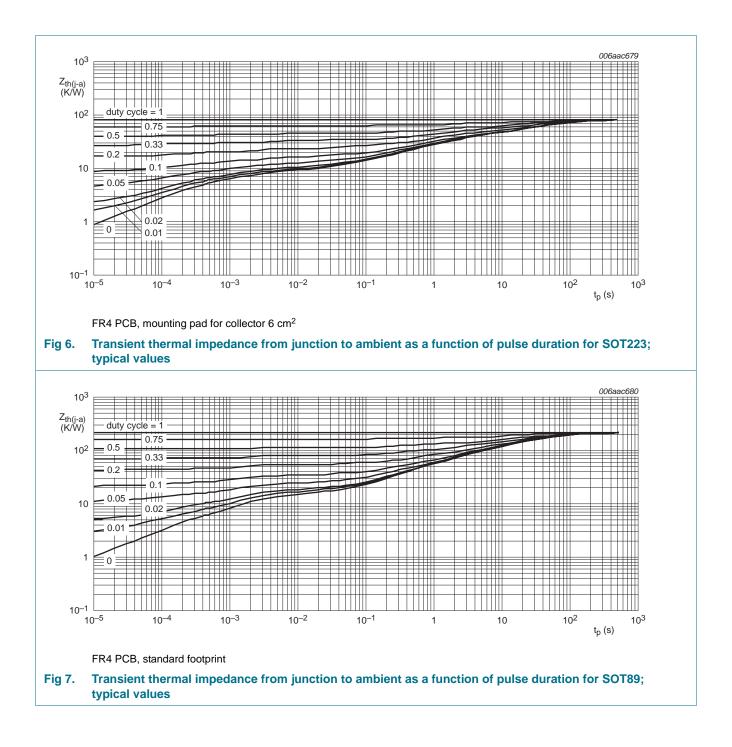
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

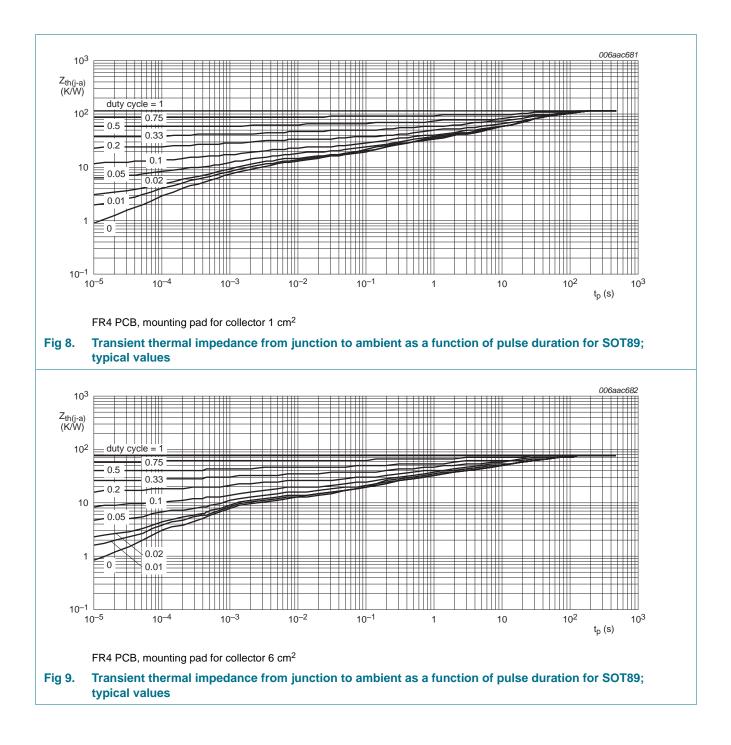
BCP56; BCX56; BC56PA



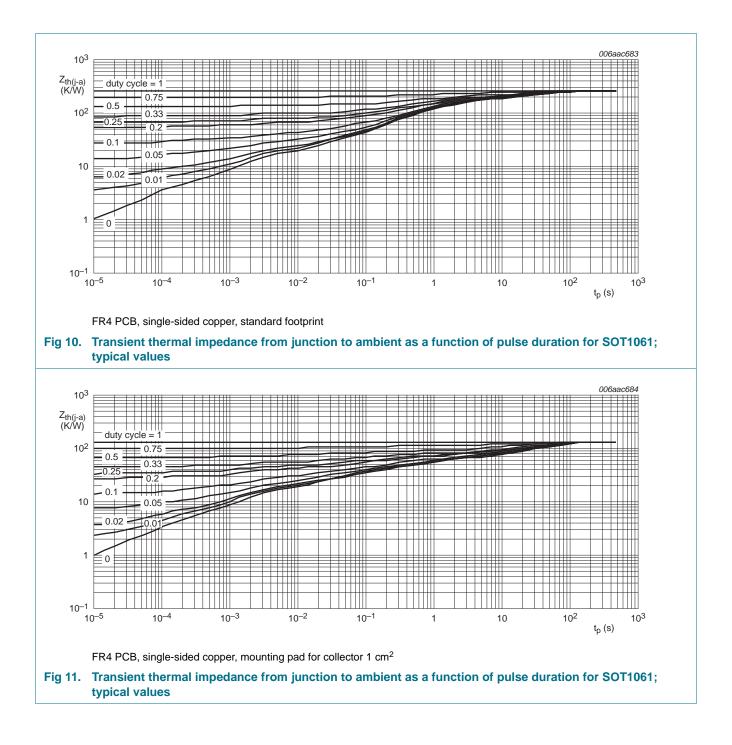
BCP56; BCX56; BC56PA



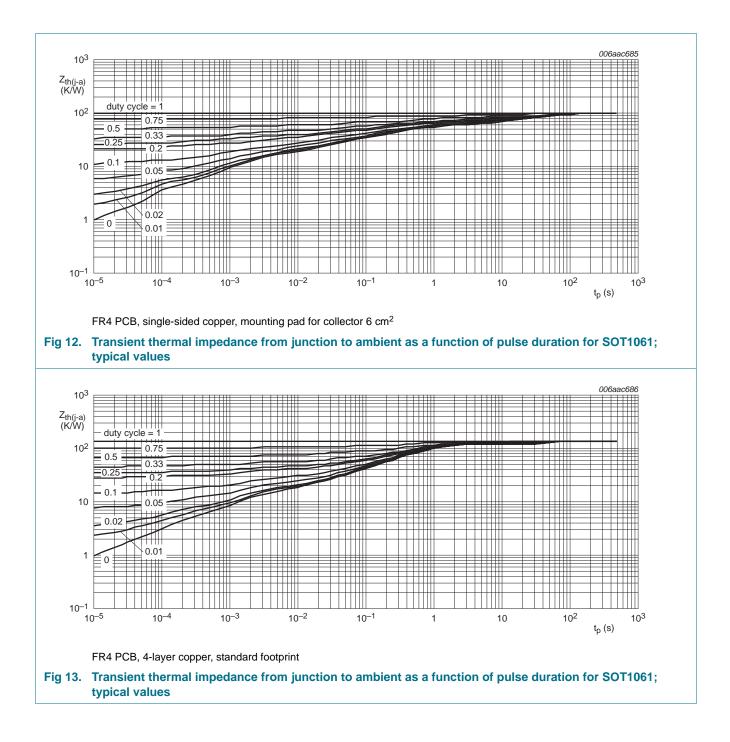
BCP56; BCX56; BC56PA



BCP56; BCX56; BC56PA

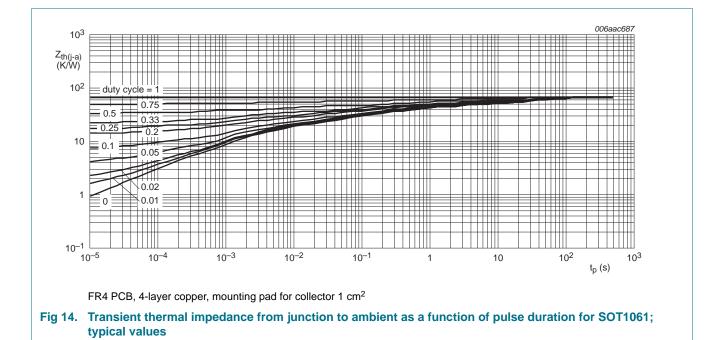


BCP56; BCX56; BC56PA



BCP56; BCX56; BC56PA

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7. Characteristics

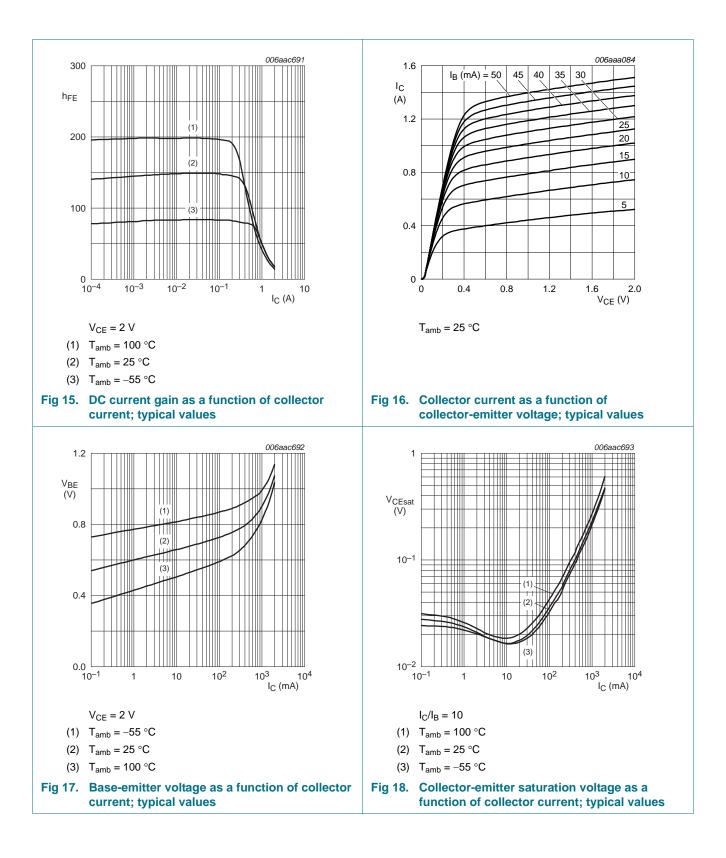
Table 8. Characteristics

 $T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Mir	п Тур	Мах	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
	current	$\label{eq:VCB} \begin{array}{l} V_{CB} = 30 \ V; \ I_{E} = 0 \ A; \\ T_{j} = 150 \ ^{\circ}C \end{array}$	-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE} DC current gain		$V_{CE} = 2 V$				
	$I_{\rm C} = 5 \rm{mA}$	<u>[1]</u> 63	-	-		
	I _C = 150 mA	<u>[1]</u> 63	-	250		
	I _C = 500 mA	<u>[1]</u> 40	-	-		
	DC current gain	$V_{CE} = 2 V$				
	h _{FE} selection -10	I _C = 150 mA	<mark>[1]</mark> 63	-	160	
	h _{FE} selection -16	I _C = 150 mA	[<u>1]</u> 100) -	250	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C}$ = 500 mA; $I_{\rm B}$ = 50 mA	<u>[1]</u> -	-	0.5	V
V _{BE}	base-emitter voltage	$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 500 \text{ mA}$	<u>[1]</u> -	-	1	V
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz} \end{array}$	-	6	-	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 50 mA; f = 100 MHz	100) 180	-	MHz

[1] Pulse test: $t_p \le 300 \ \mu$ s; $\delta = 0.02$.

BCP56; BCX56; BC56PA



BCP56_BCX56_BC56PA

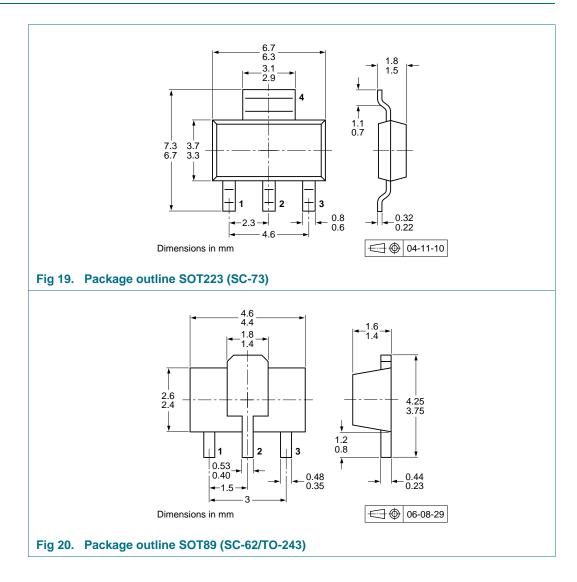
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8. Test information

8.1 Quality information

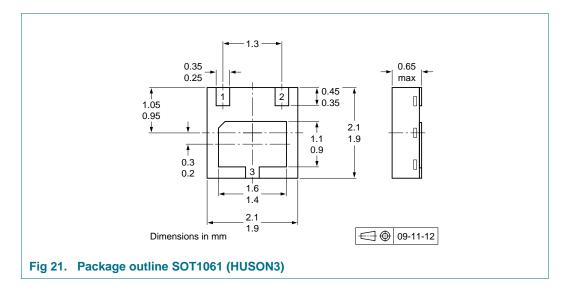
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



BCP56_BCX56_BC56PA

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10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Package Description		Package		Packir	ig quant	ity
			1000	3000	4000	
SOT223	8 mm pitch, 12 mm tape and reel		-115	-	-135	
SOT89	8 mm pitch, 12 mm tape and reel; T1	[3]	-115	-	-135	
	8 mm pitch, 12 mm tape and reel; T3	[4]	-146	-	-	
SOT1061	4 mm pitch, 8 mm tape and reel		-	-115	-	
	SOT223 SOT89	SOT2238 mm pitch, 12 mm tape and reelSOT898 mm pitch, 12 mm tape and reel; T18 mm pitch, 12 mm tape and reel; T3	SOT2238 mm pitch, 12 mm tape and reelSOT898 mm pitch, 12 mm tape and reel; T18 mm pitch, 12 mm tape and reel; T3[4]	SOT223 8 mm pitch, 12 mm tape and reel -115 SOT89 8 mm pitch, 12 mm tape and reel; T1 3 -115 8 mm pitch, 12 mm tape and reel; T1 4 -146	SOT223 8 mm pitch, 12 mm tape and reel -115 - SOT89 8 mm pitch, 12 mm tape and reel; T1 3 -115 - 8 mm pitch, 12 mm tape and reel; T1 3 -115 - 8 mm pitch, 12 mm tape and reel; T3 4 -146 -	

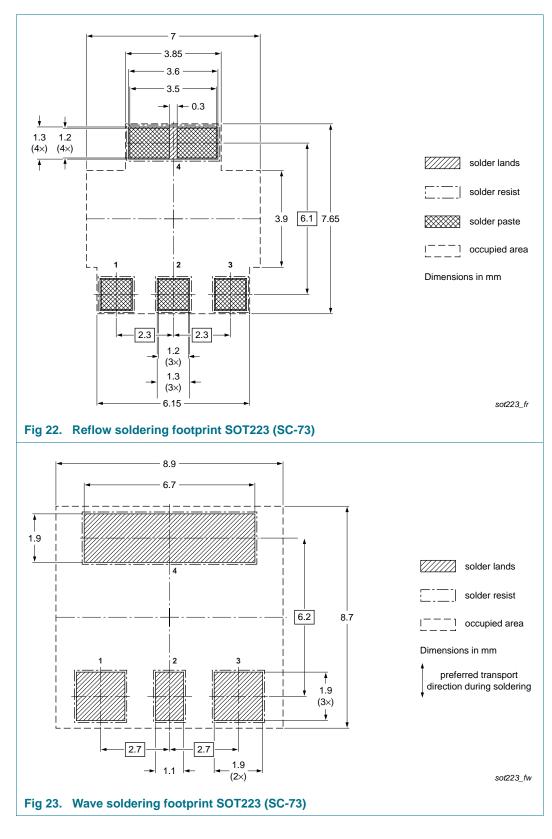
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

[2] Valid for all available selection groups.

- [3] T1: normal taping
- [4] T3: 90° rotated taping

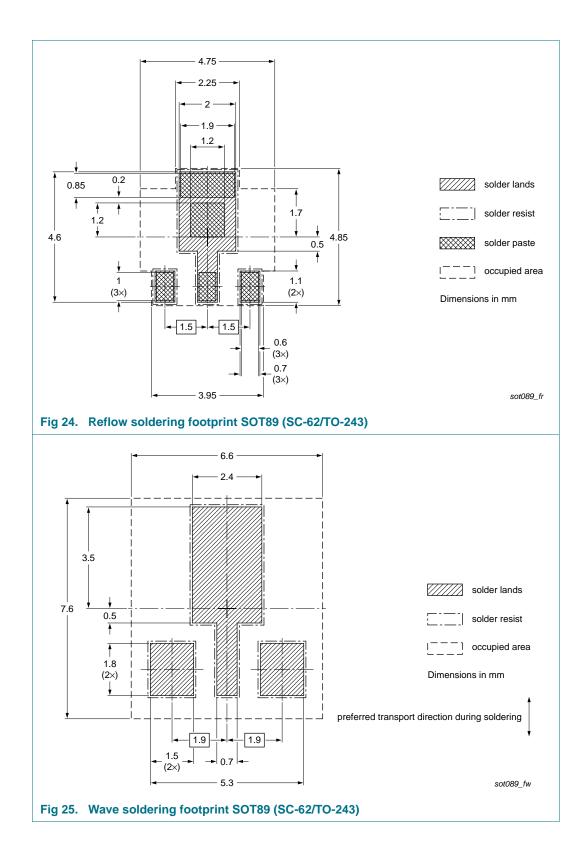
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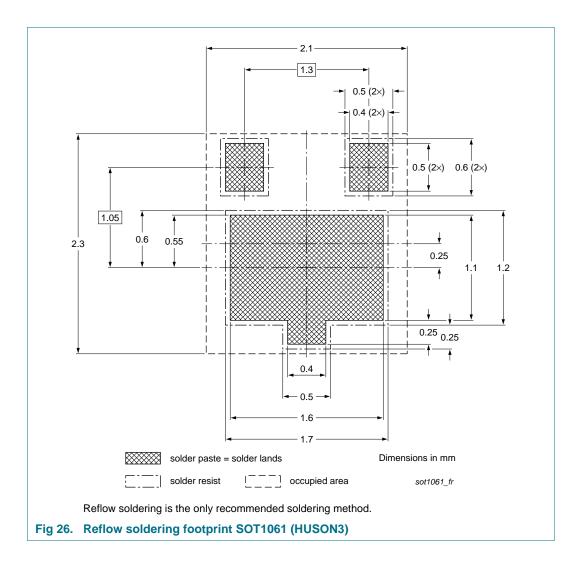
11. Soldering



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BCP56_BCX56_BC56PA





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12. Revision history

Table 10.Revision history

A and BC56-16	BC639_BCP56_BCX56 v.8
measurement	6PA
measurement	
measurement	
	S
	S
	ts
ام م ا	
dated	
	BC639_BCP56_BCX56 v.7
	BC639_BCP56_BCX56 v.6
PCN2004050	BC635_637_639 v.4
	BCP54_55_56 v.5
	BCX54_55_56 v.4
	BC635_637_639 v.3
	BCP54_55_56 v.4
	BCX54_55_56 v.3
	CN2004050

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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